Operation of a Microfabricated Planar Ion-trap for Studies of a Yb$^+$–Rb Hybrid Quantum System

Abasalt Bahrami$^{1,}$*, Matthias Müller$^1$, Martin Drechsler$^{1,}$†, Jannis Joger$^2$, Rene Gerritsma$^2$, Ferdinand Schmidt-Kaler$^1$

$^1$ QUANTUM, Institut für Physik, Universität Mainz, Staudingerweg 7, 55128 Mainz, Germany
$^2$ Van der Waals-Zeeman Institute, Institute of Physics, University of Amsterdam, Science Park 904, 1098 XH Amsterdam, The Netherlands

**Key words:** Ion trap, Atom trap, Atom-ion interaction

* Corresponding author: e-mail abahrami@uni-mainz.de
† Present address: Departamento de Física, FCEyN, UBA and IFIBA, Conicet, Pabellón 1, Ciudad Universitaria, 1428 Buenos Aires, Argentina.

In order to study interactions of atomic ions with ultracold neutral atoms, it is important to have sub-µm control over positioning ion crystals. Serving for this purpose, we introduce a microfabricated planar ion trap featuring 21 DC electrodes. The ion trap is controlled by a home-made FPGA voltage source providing independently variable voltages to each of the DC electrodes. To assure stable positioning of ion crystals with respect to trapped neutral atoms, we integrate into the overall design a compact mirror magneto optical chip trap (mMOT) for cooling and confining neutral $^{87}$Rb atoms. The trapped atoms will be transferred into an also integrated chip-based Ioffe-Pritchard trap potential formed by a Z-shape wire and an external bias magnetic field. We introduce the hybrid atom-ion chip, the microfabricated planar ion trap and use trapped ion crystals to determine ion lifetimes, trap frequencies, positioning ions and the accuracy of the compensation of micromotion.

1 Introduction

The development of laser cooling techniques to cool neutral atoms below μK temperatures and magnetic trapping has paved the way to explore quantum degeneracy in atomic gases [1,2] to investigate a variety of quantum many-body phenomena [3,4]. On the other hand Paul traps use radio-frequency (RF) driven electric fields and static voltages (DC) to trap ions in a time-averaged trapping potential [5].

Recently, the interactions between neutral atoms and charged ions have been addressed for investigations of low temperature chemical reaction [6,7,8], the study of polaron physics [9], but also to allow for novel types of quantum simulation [10]. From the experimental side, the challenge is to combine both trapping techniques into a hybrid atom-ion trap to study the atom-ion system. At large inter-nuclear separations the collisions between ions and neutral atoms are dominated by an attractive polarization potential of the form

$$V = -\frac{\alpha_p q^2}{(4\pi\varepsilon_0)^2 r^4}, \quad (1)$$

where $r$ is the inter-nuclear separation, $q$ the charge of the ion, $\alpha_p$ the isotropic static electric dipole polarizability of the neutral atom and $\varepsilon_0$ the vacuum permittivity [11]. In the s-wave scattering limit the characteristic length scale of the interaction of the potential is given by

$$r^* = \sqrt{\frac{\mu\alpha_p q^2}{(4\pi\varepsilon_0\hbar)^2}}, \quad (2)$$

where $\mu = m_im_a/(m_i + m_a)$ is the reduced mass of the two particles involved in the collision and $\hbar$ is the reduced Planck constant [12]. At this separation of the particles the characteristic energy scale $E^* = \hbar^2/2\mu r^2$ can be assigned. For the specific case of $^{87}$Rb atoms interacting with Yb$^+$ ions, $r^* = 307$ nm [13], in contrast to short-range interactions, e.g. for $^{87}$Rb atoms which requires a
A center of the atomic double-well potential can control the motion of a bosonic Josephson junction coupled to a single or a string of trapped ions (Fig. 1). A single ion trapped in the center of the atomic double-well potential can control the interactions of a bosonic Josephson junction coupled to a single or two species. A charge transfer process between \( B \) and \( A^+ \) may take place in the following ways: radiative charge transfer, photoassociative charge transfer or non-radiative charge transfer. (4) An atom-ion pair in the excited continuum may decay spontaneously to an optimal optical access and making the two traps more robust to temporal drifts of the positions of the two species. An atom-ion pair may undergo an elastic collision. The atom-ion scattering cross-section in elastic collisions \( \sigma_{el}(E) \) is described by

\[
\sigma_{el}(E) = \pi \left( 1 + \frac{\pi^2}{16} \right) r^* \frac{\hbar^2}{m \mu^2 E} \frac{1}{1/3},
\]

where \( E \approx k_B T_{\text{ion}} \). To resolve the interactions between the atoms and ions on the length scale of \( r^* \), we need to have a sub-\( \mu \)m accuracy in positioning the ions. In order to position the trapped ions with such accuracy we have to use an ion trap which has enough DC electrodes to confine ions in different trapping regions and position them accurately. For this purpose we use a segmented planar ion trap with 21 DC electrodes which can be independently controlled. By applying DC voltages to each of the opposing DC electrodes ions can be transported all along the trap axis. To investigate the interactions between atoms and ions, we have to spatially overlap the atomic cloud and ion crystals in a single apparatus. A novel atom-ion trap introduced here combines a planar ion trap with an integrated atom trap into a single chip trap (Fig. 7). This new chip design implies an infrastructural simplification of the setup featuring an optimal optical access and making the two traps more robust to temporal drifts of the positions of the two species to each other.

Our setup is aiming for studies of the tunneling dynamics of a bosonic Josephson junction coupled to a single or a string of trapped ions (Fig. 1). A single ion trapped in the center of the atomic double-well potential can control the atomic tunneling rate via spin-dependent atom-ion interactions. Since in this proposal a trapped ion can control many-body tunneling dynamics, mesoscopic entanglement between the atomic matter wave and the spin of the ion may be created. The interplay between the spin-dependent tunneling and the inter-atomic interactions could also result in superposition of quantum self-trapping and Josephson tunneling. Single, neutral impurities have also been proposed as a means to control and measure the dynamics in Josephson junctions, but these typically lack the sub-\( \mu \)m controllability offered by the trapped ion system. We can make tightly confined atomic clouds that have small sizes. This allows to limit the interactions between atoms and ions to the central region of the ion trap, where micro-motion induced heating is small. It may also put the 1D regime of atom-ion systems within reach, where the trapped ions may induce large effects in the atomic cloud, such as density bubbles.

The paper is structured as follows: First, we give an overview of the experimental design, then present the atom trap, the ion trap, its operation with successful trapping of \( Yb^+ \) ions and discuss the characterization of the ion trap. Finally we give an outlook of our upcoming experiments in the end. Initial experiments in the hybrid system of interacting ions and atoms have been plagued by micro-motion induced heating such that we address this issue specifically in our setup.

**2 System overview** Our setup consists of a hybrid atom-ion chip that can trap laser cooled neutral \( ^{87} \text{Rb} \) atoms in a mirror-magneto optical trap (mMOT) and transfer them into a tight Ioffe-Pritchard (IP) potential. The IP trap is created by a Z-shape wire together with a bias.

### Table 1 Possible processes during two-body collisions of a hetero-nuclear ion \( A^+ \) with an atom \( B \) at low energy.

| Types of processes | \( (1) A^+ + B \rightarrow A^+ + B \) | \( (2) A^+ \left| \downarrow \right> + B \left| \uparrow \right> \rightarrow A^+ \left| \uparrow \right> + B \left| \downarrow \right> \) | \( (3) A^+ + B \rightarrow A + B^+ \) | \( A^+ + B \rightarrow A + B^+ + \gamma \) | \( A^+ + B \rightarrow (AB)^+ + \gamma \) | \( A^+ + B \rightarrow A^+ B + \gamma \) |
|-------------------|------------------------|------------------------|------------------------|------------------------|------------------------|------------------------|
| Elastic collisions | Spin exchange           | N-radiative charge transfer | Radiative               | Photoassociative       | Molecule formation     |

**Figure 1** A Bose-Einstein condensate trapped in a double-well potential with an ion in the center. The internal state of the ion is controlled by laser light and controls the tunneling rate \( J \).
Figure 2 The atom trap is composed of an octagonal chip with an outside diameter of 45 mm which is used as the surface for the atom trap wires but also as a filter board and support of the ion trap. This direct mounting assures the required positioning accuracy. In the assembly of atom-ion chip, the ion trap is glued on top of the atom trap covering the central region of the octagon. Electrical bonding wires connect the DC and RF voltage from the octagon to the ion trap chip (Fig. 2). Underneath the octagon chip surface there are a big U-shape, a small U- and a Z-shape wires. It is also schematically shown how electric current can flow in the wires during the trapping phase (red arrows) to form the magnetic field configuration required for a mMOT or IP trap. The filter board includes 3.38 MHz low-pass filters ($C = 4.7 \, \text{nF}$, $R = 10 \, \Omega$) on the DC control electrodes to filter RF pickups.

magnetic field (Fig. 4) and we expect trap frequencies of $(\omega_x, \omega_y, \omega_z) = 2\pi \times (1170, 1167, 84) \, \text{Hz}$ from our calculations. Atoms trapped in this IP potential are spatially overlapped with an Yb$^+$ ion crystals which are loaded into a microfabricated planar Paul trap (Fig. 4).

For cooling and trapping of Rb atoms near the surface of the ion trap, we use the chip trap in a mMOT configuration [28]. Rb atom sources are two dispensers (SAES Getters), one implemented behind and one in front of the atom-ion trap (Fig. 2). The atom trap shown in Fig. 2 is fabricated using thick film technology in order to print UHV-compatible, sub-mm-scaled electrical circuits on the Alumina substrate (Al$_2$O$_3$). A major benefit of using this technology is the possibility of printing multiple circuit layers separated by isolating layers which we used for our design.

In order to realize a mMOT, we need two $\sigma^+$ circular polarized and two $\sigma^-$ circular polarized laser beams and a quadrupole magnetic field (Fig. 3). Our Rb-laser system consists of two home-made external cavity diode lasers (Panasonic LNC728PS01WW) with a maximum output power of 200 mW at continuous wave condition. These lasers are individually frequency stabilized to the atomic transitions in the D2 line of $^{87}$Rb ($5^2S_{1/2} \rightarrow 5^2P_{3/2}$) through frequency modulation spectroscopy. The cooling laser frequency is locked to the crossover transition CO(2,3) and the repump laser to the $F = 1 \rightarrow F' = 2$ transition. To extract information from an atomic cloud, we use an additional laser beam for absorption imaging [29]. We take time-of-flight (TOF) images with a probe beam pulse resonant with the $5^2S_{1/2}(F = 2) \rightarrow 5^2P_{3/2}(F = 3)$ transition, which casts a shadow on a CCD camera (Pco.pixelfly with 1392 $\times$ 1040 px$^2$). To get a good signal the probe beam intensity must be below saturation which is for $\pi$-polarized light $I_{\text{sat}} = 2.50 \, \text{mW/cm}^2$ with the resonant cross section $\sigma = 1.9 \times 10^{-9} \, \text{cm}^2$ [30].

The axially symmetric quadrupole field is generated by a pair of current carrying coils (mMOT coils) in anti-Helmholtz configuration. The mMOT coils are 45°-rotated with respect to the plane of the trap. The distance between the two coils is 27 cm and each coil consists of 36 turns of a hollow-core copper wire with a quadratic cross section (outer diameter 6 $\times$ 6 mm$^2$ and an inner diameter 4 $\times$ 4 mm$^2$) wrapped in Kapton tape for electrical insulation. These coils are internally cooled down to 20°C with a 300 Watts chiller (MINORE 0 RB400). At a maximum current of 200 A supplied by a high power source (SM 30-200 Delta Elektronica), we measure a magnetic field gradient of $\partial B_{\text{axial}} / \partial r_{\text{axial}} = 0.11 \, \text{T/m}$ at the center of the trap which is at a few mm from the ion trap surface. Measured magnetic field gradients are in the range of 0.10 – 0.20 T/m for proper trapping efficiency [31].

Figure 3 (a) mMOT showing configuration of the laser beams and the quadrupole magnetic field. (b) The magnetic field gradient along the axial direction of mMOT coils. The dashed line is the simulation using Radia software [32] and solid line is the measurement.
Once atoms are captured in the mMOT, the mMOT coils will be switched to a bias field while switching on the big U-shape wire beneath the atom chip which generates a quadrupole field with a minimum at infinity. The atoms can now be confined at about 2 mm underneath the chip surface in a spatially smaller area. The atoms will then be transferred to a potential created by the small U-shape wire in the atom chip. At this step we shift the atoms close to the ion trap surface and compress the atom cloud to a smaller and steeper mMOT volume. As the final step we create an Ioffe-Pritchard trap by turning on the Z-shape wire in the atom chip together with a bias magnetic field (Fig. 4). The axial direction of the atom cloud trapped in the magnetic field of the Z-shape wire is not necessarily parallel to the z-axis of the ion trap. In the atom trap design we have considered the length of the Z-shape wire to be 1.4 mm, so that the atom cloud overlaps with the ion cloud (Fig. 2).

The ion trap we use in the experiment (Fig. 5) is a microfabricated surface trap with 21 DC electrodes which is fabricated in Translume technology [33,34]. A pulsed laser is used to pattern trenches of 50 µm deep and 10 µm wide in a fused silica substrate (SiO₂). Then material is etched with hydrofluoric acid which has a strong corrosive characteristic against SiO₂. Finally the surface is coated with four metal layers of 20 nm Titanium, 150 nm gold, 20 nm Titanium and 150 nm gold, i.e. 300 nm gold in total. The ion trap is glued on top of the atom trap using a UV adhesive (EPO-TEK® OG142-112 UV Cure Optical Epoxy) (Fig. 7). The adhesive is carefully applied at the edges of the ion trap while preventing the adhesive to run between the two traps and is cured by illuminating it three times for 10 s with UV light. The electric connections between the ion trap and the filterboard are established by wire bonds (25 µm diameter Pd wire). Planar Paul traps with characteristic length of about 100 µm have advantages in terms of fabrication and scalability [35,36,37,38,39,40,41]. In planar traps the ions are confined radially by RF potentials and axially by static electric voltages (DC) and all electrodes lie in a single plane [42]. There are several analytical approaches like a model by House [43] and Biot-Savart-like methods [44,45,46] to design planar traps with arbitrary geometries. In this report we use the House model for analytical determination of the applied DC and RF potentials.

Figure 4 (Color online) Potentials and $B$-fields of the Z-shape wire in z-x, x-y and z-y planes with minimum at $x_0 = 0$ mm, $y_0 = 0.070$ mm and $z_0 = 0$ mm. Every color-step in contour plots corresponds to 1 Gauss.

Figure 5 Optical microscope image of the microfabricated surface trap used in our experiment. The chip has a size of $9 \times 4.5$ mm$^2$ and a thickness of 500 µm. It has a long and symmetric F-shape rail for RF confinement, 20 static-voltage electrodes with a size of $200 \times 200$ µm$^2$ used for the radial confinement (E01 - E20) and one inner compensation electrode which is axially and symmetrically extending along a slit of 100 µm width and 5 mm length (E21). This slit is used to load Rb atoms from a dispenser placed right behind the ion trap. In the experiments described here, Yb$^+$ ion crystals are trapped and confined along the trap axis ($z$-direction). The gaps between the electrodes are approximately 10 µm wide and 50 µm deep, which are large enough that the RF voltage does not cause electrical breakdown at $100 - 200$ V$_{pp}$. 

Copyright line will be provided by the publisher
Figure 6 Overview of the system: 1. NEG pump 2. Trap carrier with Rb atom source 3. Hybrid trap 4. mMOT coils 5. Rb and Yb atom sources. The trap is mounted upside down on a home-made carrier which is attached to a special CF63 flange featuring various electrical feedthroughs. The trap surface is right in the middle of the vacuum chamber. Using a weld bellow (CF35/SEWB) one can adjust atom sources relative to the trap chip.

to trap Yb\(^+\) ions. The assembled trap is shown in Fig. 7 where the atom-ion chip is mounted upside-down on a carrier which is attached to a CF63 having various electrical feedthroughs. The chip surface is right in the middle of the vacuum chamber which guarantees optimal optical access [47]. Fig. 6 shows the complete vacuum setup and its main functional parts. Seven anti-reflection coated fused quartz silica viewports allow laser access to the center of the ion trap and the atom trap. The distance between the hybrid trap and the surface of the big window is 85 mm. To reach a UHV pressure, an ion getter pump (NEXTorr \(D200-5\)) is attached to a cross right next to the chamber. The pressure we reach in our chamber is \(1.3 \times 10^{-6}\) hPa.

3 Observation of ions We introduce our surface trap which has a F-shape RF electrode for axial confinement of the ions. For the radial confinement it has 20 DC electrodes, which are placed axially symmetric around the RF rail and one compensation electrode in-between the legs of the RF (Fig. 3). Optical resolution of our imaging system is about 720 nm and we typically trap Yb\(^+\) ions at a distance of 150 µm to the surface of the trap and can position them axially with an accuracy of about ± 80 nm, see Sec. 4.

4 Ion trap operation The configuration of our Paul trap is linear, thus radial confinement is achieved by applying a RF sinusoidal drive field. Ions are confined in the node line of the quadrupole field that is generated from the electrodes. This harmonic binding in the radial r1 and r2 directions is described by a pseudopotential \(\Phi_{RF}\). Additionally, ions or ion crystals, are confined along the trap z axis by a DC harmonic oscillator potential \(\Phi_{DC}\). In the full description, both, RF and DC fields are independently adjusted for controlling the ion crystals position and alignment, the inter-ion distances, and the trapping frequencies in all directions. The challenge is to find control voltages that suite the experimental protocol, and also match the condition that the center of the DC potential falls on the RF node line, where the ion micromotion is compensated (see Sec. 4.1).

The total effective potential for trapping the ions \(\Phi (r, t)\) is given by the sum of a time-independent potential \(\Phi_{DC}\) generated by the trap DC electrodes and a sinusoidally varying part, the pseudopotential, \(\Phi_{RF}\) that is driven by a RF voltage source:

\[
\Phi (r, t) = \Phi_{RF} + \Phi_{DC}
\]

\[
= \frac{q^2 V_{RF}^2}{4M \Omega_{RF}^2} ||\nabla \phi_{RF}||^2 + Q \sum V_i \phi_{DC,i},
\]

here, \(q\) and \(M\) are the charge and mass of the trapped ions. \(V_{RF}\) and \(\Omega_{RF}\) denote the RF amplitude and frequency, respectively. The potential terms \(\phi_{RF}\) and \(\phi_{DC}\) are the solution of the Laplace equation for a unit voltage applied to the RF and the \(i\)th DC electrode. \(V_i\) is the voltage applied on the \(i\)th DC electrode. Radial confinement of ions is realized by applying a RF voltage at a frequency of \(\Omega_{RF} = 2 \pi \times 11.22\) MHz and an amplitude of 109 V\(_{pp}\). This RF signal is generated by a RF generator (Rohde \& Schwarz SML01), amplified (ZHL-5W-1-Mini Circuits) and sent to a helical resonator with a Q-factor of 100.

Figure 7 Final assembly of the atom-ion chip with all wire-bonds. The atom source carrier is placed below the trap carrier and it includes a Rb atom dispenser and the Yb atom oven.
Figure 8 Energy level scheme of the electronic ground and excited states of $^{171}$Yb$^+$ with nuclear spin $I=1/2$; the isotopes we have trapped are without nuclear spin. The transitions driven by diode lasers in our experiment are marked as straight lines. Life times and decay branching ratios are taken from $^{53}$. Additional low-lying $^2D_{5/2}$ and $^2P_{7/2}$ states have been omitted for clarity.

360 to further enhance the signal $^{43}$. With these values we reach a relatively small trap depth of 50 mV. In order to filter RF pickups, we have implemented a 3.58 MHz low-pass filter on the chip connected to each DC electrode (Fig. 2) and a second 50 kHz low-pass filter connected to the feedthrough. At our typical RF voltages of $116 - 930$ mV$_{pp}$ in the DC electrodes. Trapped ions are confined with typical trap frequencies of $(\omega_z, \omega_x, \omega_y) = 2 \pi \times (485, 724, 289)$ kHz, where $\omega_z$ is the axial and $\omega_x$ and $\omega_y$ are the radial trap frequencies of the ion tap.

To provide the voltage for the DC electrodes, we use FPGA-controlled digital-to-analog conversion (DAC) boards. They allow sweeping voltages in real time and avoid delays caused by PCs. The ion transport will be achieved by shifting the DC potential minimum. Therefore, ultra-fast voltage update rates need to be incorporated. This makes the use of FPGA controlled DACs necessary $^{49, 50}$. Hence, the design we use is mainly comprised of a high-speed and low noise advance multichannel arbitrary waveform generator (N-MCWG) developed at the University of Mainz $^{51}$. It supports up to 48 independent analog channels (16 bits) and 25 digital TTL signals per unit. Analog channels have a voltage range of $-10$ V to $+10$ V with a resolution of $(0.12 \text{ mV})$ LSB.

The Yb laser system consists of three lasers used to ionize, cool and excite dipole transition of the Yb$^+$ ions. For the initial steps we rely on $^{174}$Yb$^+$, while in the further run $^{171}$Yb$^+$ with a long lived spin $1/2$ system of ground states $^2S_{1/2}(F = 0)$ and $^2D_{3/2}(F = 1)$ will serve as qubit. The relevant level structure of $^{171}$Yb$^+$ is shown in Fig. 8. To isolate-selectively ionize neutral Yb atoms, we use a two-step photoionization scheme $^{53}$. First we excite the neutral Yb atoms from $^1S_0 \rightarrow ^1P_0$ with a home-made grating-stabilized diode laser at 398.9 nm ( Nichia NDHU110APAE2). The first step excitation is impinging the atomic beam under right angle and allows for isotope-selective excitation and trap loading $^{54, 55}$. We use a Toptica TA-SHG pro as second step to the continuum and for cooling of $^{174}$Yb$^+$ ions, by exciting the $^2S_{1/2} \rightarrow ^2P_{1/2}$ transition ($\Gamma = 19.7$ MHz), which yields to laser-induced fluorescence for single ion detection at a wavelength of 369.5 nm. Ions in the $^2P_{1/2}$ state can decay to the lower lying $^2D_{3/2}$ state with a branching ratio of $\alpha = 0.00501(15)$. Therefore, to keep the ions in the cooling cycle, we use an additional Toptica DL pro Laser at 935.2 nm to repump from the $^2D_{3/2} \rightarrow ^2D_{3/2}(2 S_{1/2})$ state ($\Gamma = 4.2$ MHz). Both, the 369.5 nm and the 935.2 nm lasers are locked to Fabry-Pérot cavities with finesse of 630. The 369.5 nm cooling and the 398.9 nm photoionization lasers are coupled to the same polarization maintaining fiber and the outcome beam is overlapped with the 935 nm repump beam using a dichroic mirror. All beams pass through a $f = 125$ mm achromatic lens and are aligned in parallel to the surface of the trap. The beam has a slight angle of $7^\circ$ to the trap axis. The cooling beam has an effective beam diameter of $30 \mu$m at its focal point and a saturation power of about $40 \mu$W. A magnetic field of $0.13$ mT at $135^\circ$ to the laser k-vector, sets the direction of the quantization axis. The fluorescence of the ions is collected with a microscope objective with a numerical aperture of 0.35 through an inverted viewport and detected by an EMCCD (Andor Luca 8×8 $\mu$m$^2$) equipped with a band-pass filter (FB370-10); Our imaging system has a calibration factor of 1.09(7) $\mu$m/px. A linear crystal of Yb$^+$ ions trapped in our setup is shown in Fig. 2. By trapping Yb$^+$ ions, we could find the cooling and repumping laser wavelengths for $^{170}$Yb$^+$, $^{172}$Yb$^+$, $^{174}$Yb$^+$ and $^{176}$Yb$^+$ which are all nuclear-spin free isotopes. The first step ionization wavelength are extracted through the fluorescence signal of neutral Yb atoms (Tab. 2). These wavelength are in good agreement with the values stated in Ref. $^{57}$.

We measured the lifetime of a single ion under continuous Doppler cooling and in the dark. The lifetime of a Doppler cooled single ion is usually many hours but in our experiment we measured short lifetimes of 2 min only due to relatively high background gas pressure of $1.3 \times 10^{-6}$ hPa. Nevertheless these values are in good agreement with the values stated in Ref. $^{57}$.

Table 2 Yb transition wavelengths (vacuum). These values are measured using a HighFinesse wavelength meter (WS6). The $^2S_{1/2} \rightarrow ^2P_{1/2}$ and $^2D_{3/2} \rightarrow ^2D_{3/2}(2 P_{1/2})$ transition wavelengths were obtained by observing fluorescence signal levels from a trapped ion.

<table>
<thead>
<tr>
<th>Isotope</th>
<th>Ionization (nm)</th>
<th>Cooling (nm)</th>
<th>Repump (nm)</th>
</tr>
</thead>
<tbody>
<tr>
<td>$^{170}$Yb</td>
<td>398.91070(5)</td>
<td>369.52360(5)</td>
<td>935.19750(5)</td>
</tr>
<tr>
<td>$^{172}$Yb</td>
<td>398.91100(5)</td>
<td>369.52440(5)</td>
<td>935.18730(5)</td>
</tr>
<tr>
<td>$^{174}$Yb</td>
<td>398.91135(5)</td>
<td>369.52495(5)</td>
<td>935.18015(5)</td>
</tr>
<tr>
<td>$^{176}$Yb</td>
<td>398.91160(5)</td>
<td>369.52550(5)</td>
<td>935.17240(5)</td>
</tr>
</tbody>
</table>

Copyright line will be provided by the publisher.
agreement with other shallow surface Paul traps at room temperature (Tab. 3) \[58\]. The lifetime of a single ion in dark is about 1 min which is long enough for atom-ion interaction studies. In typical sequences, modifications of the loss rate are an observable at time scales of about 100 ms \[59\].

In order to effectively cool the trapped ions, we need to tilt the principal axes of the ion so that a single laser can cool all three normal modes. All three Yb laser beams are aligned in parallel to the trap surface such that there is 12% projection of its k-vector on the radial trap axis (x and y) and resulting a negligible Doppler efficiency. (Fig. 10). In order to tilt the principal axes of the ion, we apply DC voltages that are asymmetric along the x-axis. In our case the trap has a symmetric compensation and RF electrodes. Simulating our trap potential following the analytical solution given by House \[43,60\] DC voltages for tilting are calculated. To create a non harmonic potential we set the compensation electrode and one pair of opposing electrodes to different voltages and calculate the voltages for the surrounding electrodes to overlap the minimum of the DC potential and the RF node. A voltage set calculated in this way is listed in Fig. 10 which creates a tilted DC potential as shown in Fig. 11. Since we do not have control over each electrode, due to the shorts on the trap, we need to calculate special fields for electrical shorts to ground for some of the DC electrodes by neighboring electrodes. Note, that even with this constraint, the trap frequencies can be adjusted and measured values fit the theoretical expectation, see Fig. 12.

4.1 Micromotion compensation Micromotion compensation is an important necessary condition for experiments where cold atoms interact with cold trapped ions.

Figure 9 Linear crystal of $^{174}$Yb$^+$ ions trapped with corresponding trap frequencies of $(\omega_x,\omega_y) = 2\pi \times (406, 110)$ kHz. The dark ion observed to be $^{172}$Yb$^+$ isotope in most of the cases. Among the stable isotopes of Yb atom, $^{172}$Yb isotope is the second most abundant and has a photoionization energy close to $^{174}$Yb isotope. Each pixel in the image corresponds to 1.09(7) µm.

Table 3 1/e lifetimes ($\tau$) of a single $^{174}$Yb$^+$ ion trapped in different axial positions of the trap.

<table>
<thead>
<tr>
<th>Ion position</th>
<th>$\tau$ with cooling (s)</th>
<th>$\tau$ w/o cooling (s)</th>
</tr>
</thead>
<tbody>
<tr>
<td>E02, E12</td>
<td>198.4 ± 0.5</td>
<td>50.5 ± 4.3</td>
</tr>
<tr>
<td>E04, E14</td>
<td>128.6 ± 0.8</td>
<td>40.6 ± 3.3</td>
</tr>
<tr>
<td>E06, E16</td>
<td>89.5 ± 0.5</td>
<td>39.9 ± 2.7</td>
</tr>
<tr>
<td>E08, E18</td>
<td>151.6 ± 0.6</td>
<td>31.7 ± 2.6</td>
</tr>
</tbody>
</table>

In cases, where the center of the DC potential and the RF potential are not superimposed the ions will undergo a fast oscillation at the frequency of the trap drive. This shift has to be determined and corrected by applying the proper corrections to the DC potential. For this, several methods have been applied \[61,62,63\] and the best compensation achieve a residual shift of 0.7 µm at respective trap frequencies of $(\omega_x,\omega_y) = 2\pi \times (350, 50)$ kHz \[64\]. We vary the RF amplitude and observe on the CCD image how the ion position is changing. In this way, we vary the DC control voltages such that the ion position does no longer change with the variation of the RF amplitude, see Fig. 13.

A systematic measurement of the stray fields is done analogues to Ref. \[61\]. As an example we measure for the case when the ion is over electrodes E06 and E16. We set the surrounding voltages to the simulated set of Voltages shown in Fig. 10. The experimental procedure is to vary the RF gain between −20 and −15 dBm shown at the RF generator and measure the corresponding position of the ion. In each of the following steps we change the voltage of one of the surrounding DCs and repeat the RF variation and position determination. This measurement leads to a 2D plot, where the ion position is always moving towards the RF null for high RF amplitudes. If the compensation

Figure 10 Simulated voltages to produce a tilted potential between electrodes E06 and E16 where the Yb$^+$ is trapped. The alignment of Gaussian beams are also schematically shown here.

Figure 11 (color online) DC potential along x- and z-axis of the ion trap. (a) The black dotted line is a DC potential without tilting, while the solid black line is the tilted DC potential created by neighboring DC potentials shown in different colors. (b) Tilted DC potential along the axis of the ion trap (z).
the residual stray electric field \( \varepsilon_{\text{stray}} \). After the 2D compensation we estimate a residual electric stray field uncertainty of \( (\Delta \varepsilon_{\text{stray},x}, \Delta \varepsilon_{\text{stray},z}) = (0.90, 0.30) \) V/m with the corresponding trap frequencies of \( (\omega_x, \omega_z) = 2\pi \times (305, 435) \) kHz. The residual electric stray field uncertainty measured in our ion trap are sufficient enough for a first atom-ion interaction study but in the future we will extend the 2D micromotion compensation to a full 3D by using parametric resonance excitation induced by potential modulation \( [62] \).

5 Conclusion and outlook We have introduced a hybrid atom-ion experimental setup to trap the \( \text{Yb}^+ \) ions and the \( ^{87}\text{Rb} \) atoms to investigate atom-ion interaction. Our setup is a compact planar Paul trap with segmented DC electrodes, this featuring the exact positioning of single ions. We characterized the trap performance including minimization of micromotion arising from stray electric fields. Comparing the residual electric stray fields to literature the micromotion compensation should be good enough for atom-ion interactions. Controlled movement of the ions in the axial direction of the trap for about 1.6 mm is also accomplished. The next step in our experiment will be trapping \( ^{87}\text{Rb} \) atoms before we overlap them with the ion crystals in order to investigate atom-ion collision dynamics.

Acknowledgements This work was supported by the EU-STREP EQuaM and the SFB/TR49. We thank Johannes Denschlag (Univ. of Ulm), Hartmut Häffner (Univ. of California Berkeley) for support and Arezoo Mokhberi for helpful discussions.

References

We introduce a new micro-fabricated planar ion trap combined with an integrated atom trap into a single chip. Trapped single ions can be coupled to a small neutral atom cloud enabling us to investigate the atom-ion interactions. This includes the tunneling dynamics of a bosonic Josephson junction and spin dynamics of ion inside a polarized neutral atoms.